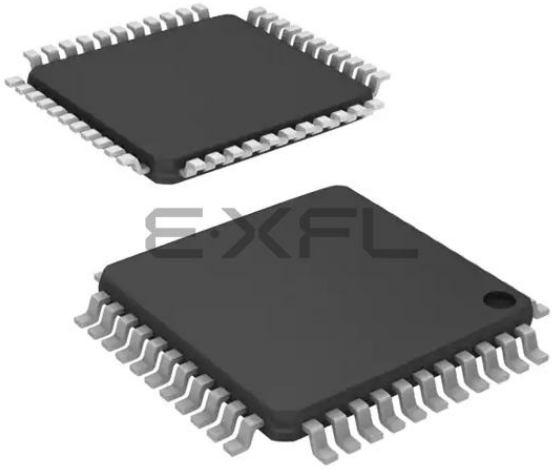

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	PIC
Core Size	8-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	36
Program Memory Size	28KB (16K x 14)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.3V ~ 5.5V
Data Converters	A/D 28x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-TQFP
Supplier Device Package	44-TQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic16f1519-i-pt

FIGURE 2-2: 28-PIN UQFN DIAGRAM FOR PIC16(L)F1512, PIC16(L)F1513, PIC16(L)F1516 AND PIC16(L)F1518

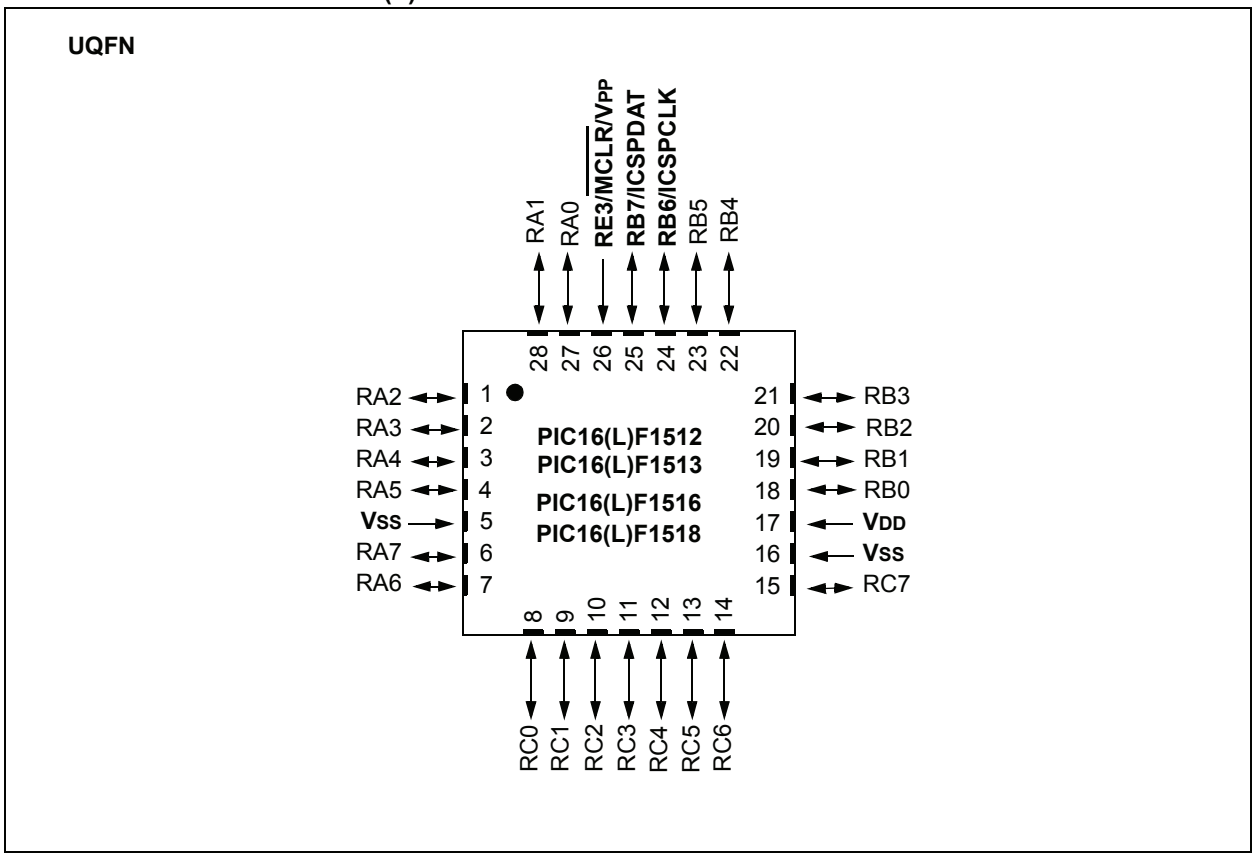


FIGURE 2-3: 40-PIN PDIP DIAGRAM FOR PIC16(L)F1517 AND PIC16(L)F1519

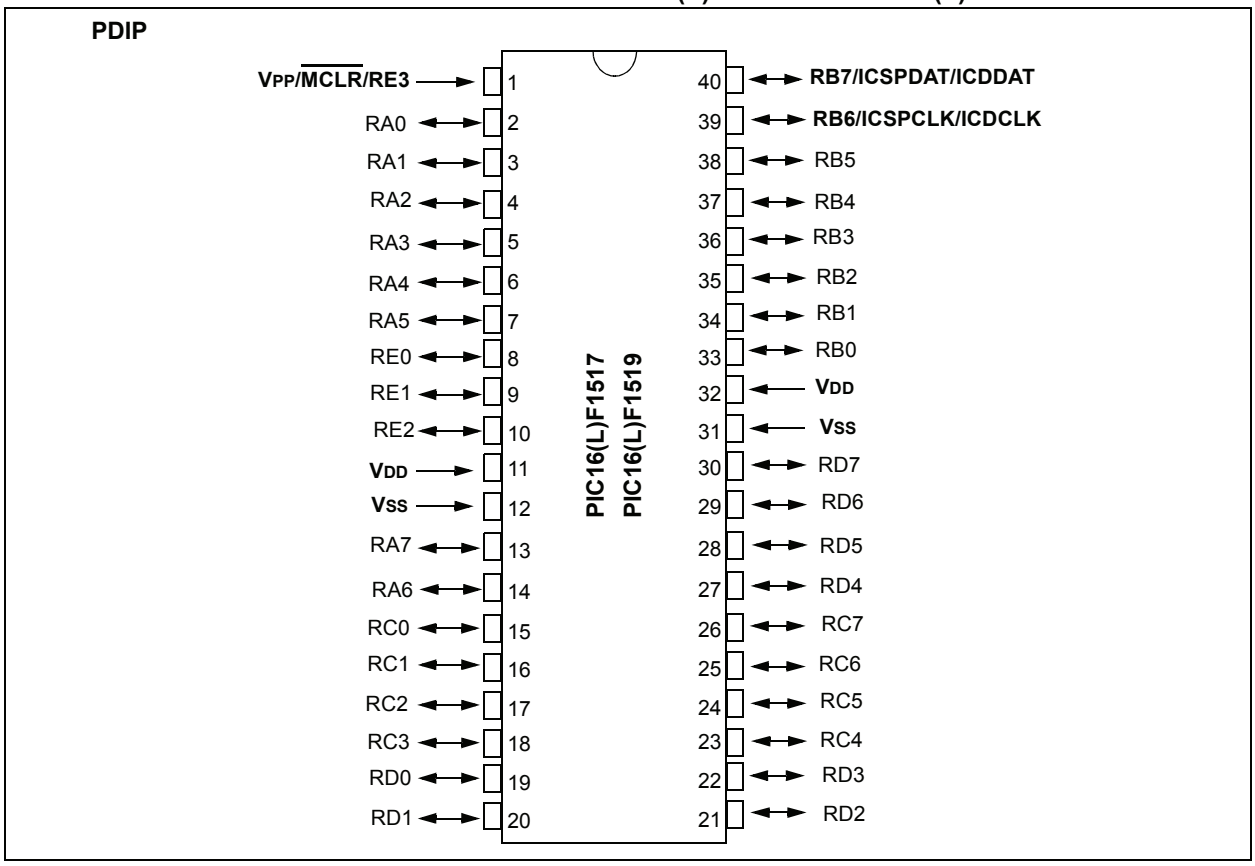


FIGURE 2-4: 40-PIN UQFN DIAGRAM FOR PIC16(L)F1517 AND PIC16(L)F1519

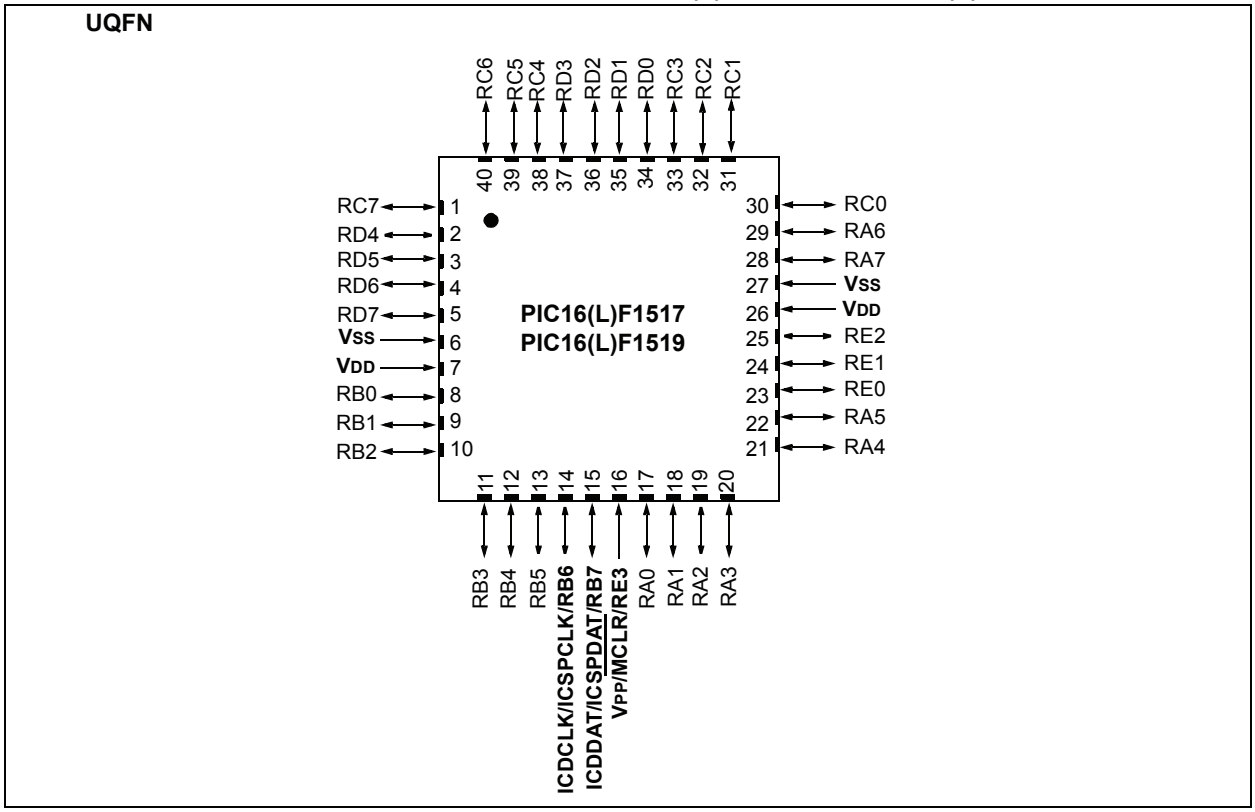


FIGURE 2-5: 44-PIN TQFP DIAGRAM FOR PIC16(L)F1517 AND PIC16(L)F1519

TQFP

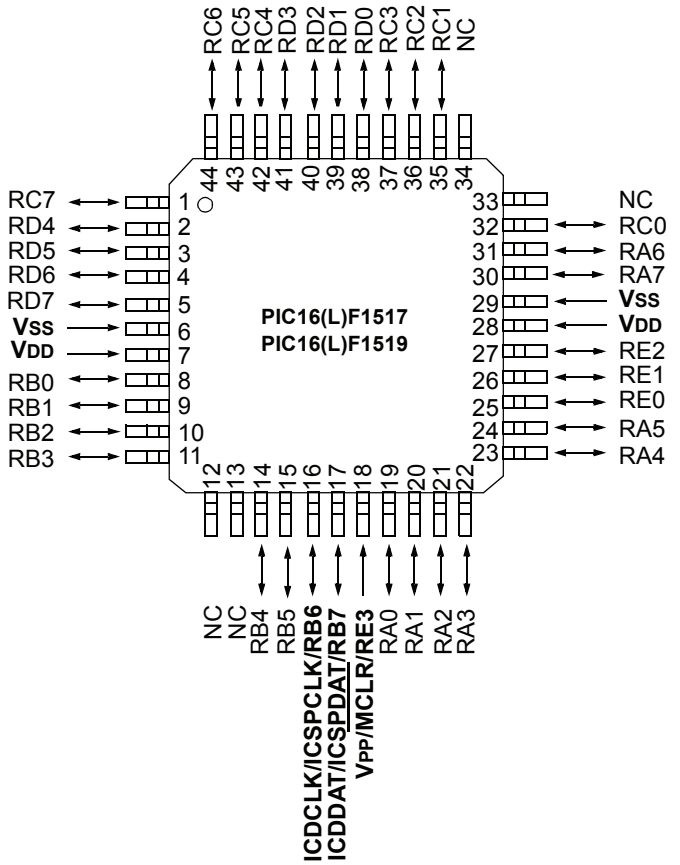


FIGURE 2-6: 64-PIN QFN DIAGRAM FOR PIC16(L)F1526 AND PIC16(L)F1527

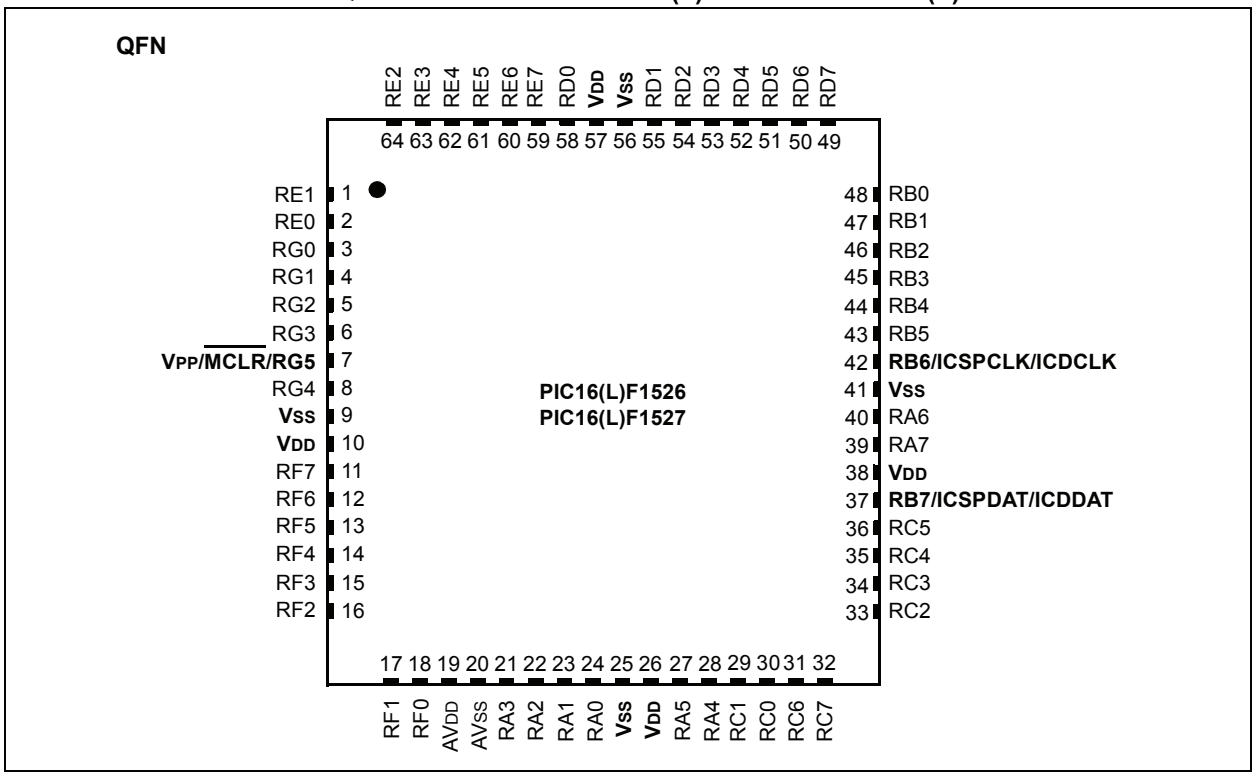


FIGURE 2-7: 64-PIN TQFP DIAGRAM FOR PIC16(L)F1526 AND PIC16(L)F1527

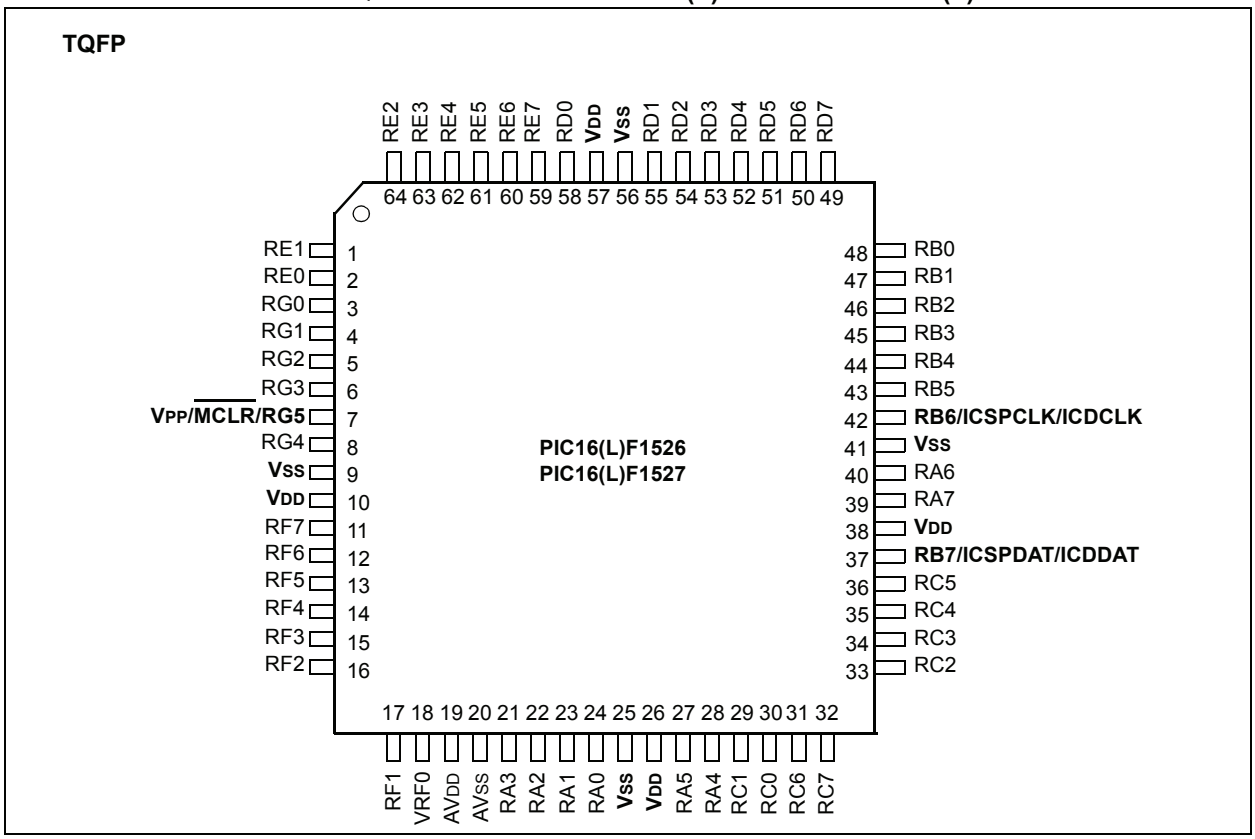
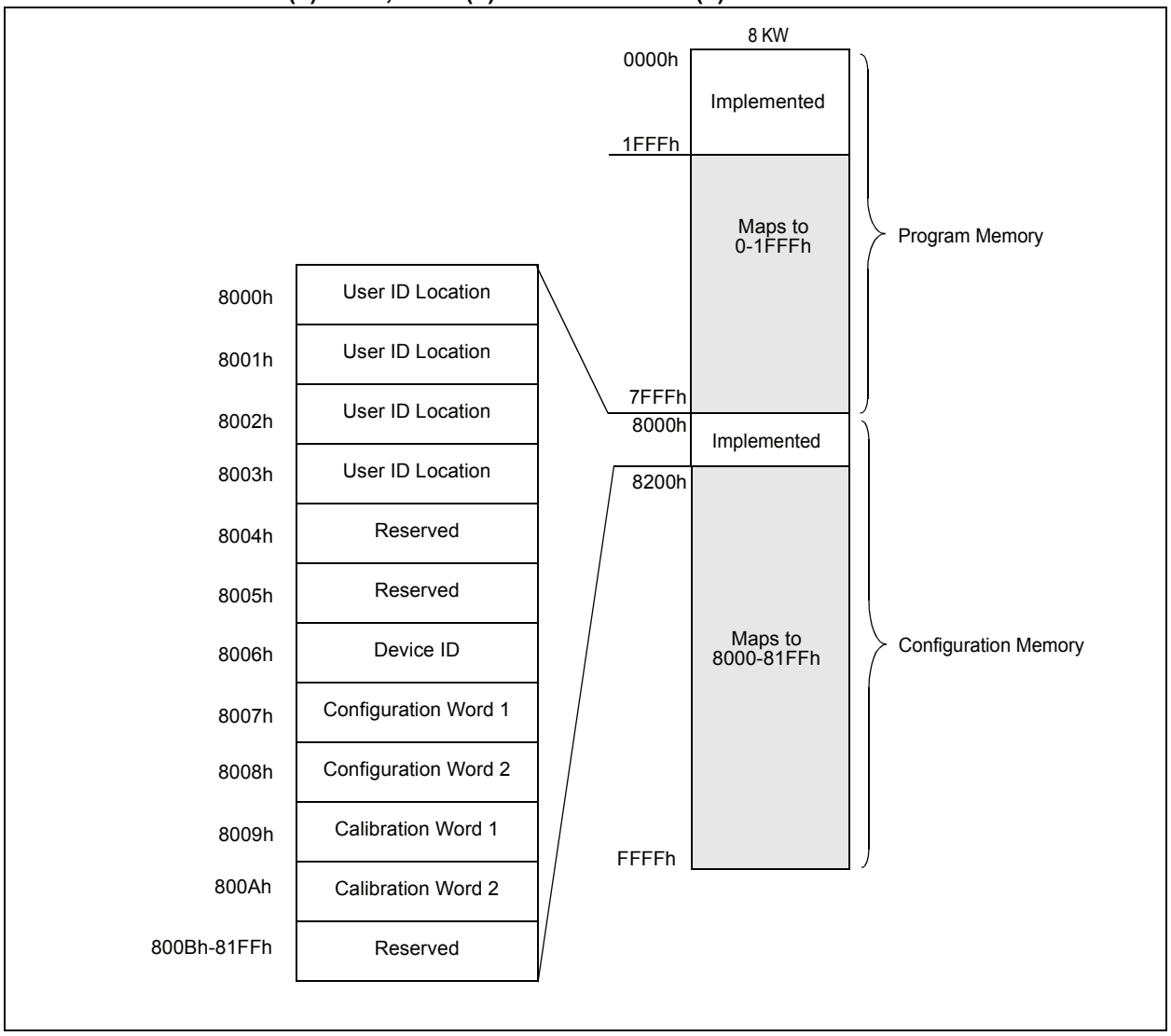


FIGURE 3-3: PIC16(L)F1526, PIC16(L)F1516 AND PIC16(L)F1517 PROGRAM MEMORY MAPPING



3.1 User ID Location

A user may store identification information (user ID) in four designated locations. The user ID locations are mapped to 8000h-8003h. Each location is 14 bits in length. Code protection has no effect on these memory locations. Each location may be read with code protection enabled or disabled.

Note:	MPLAB® IDE only displays the 7 Least Significant bits (LSb) of each user ID location, the upper bits are not read. It is recommended that only the 7 LSbs be used if MPLAB IDE is the primary tool used to read these addresses.

3.2 Device ID

The device ID word is located at 8006h. This location is read-only and cannot be erased or modified.

REGISTER 3-1: DEVICE ID: DEVICE ID REGISTER(1)

R	R	R	R	R	R
DEV<8:3>					
bit 13					bit 8

R	R	R	R	R	R	R	R
DEV<2:0>			REV<4:0>				
bit 7							bit 0

Legend:	P = Programmable bit	U = Unimplemented bit, read as ‘0’
R = Readable bit	W = Writable bit	‘0’ = Bit is cleared
-n = Value at POR	‘1’ = Bit is set	x = Bit is unknown

bit 13-5 **DEV<8:0>:** Device ID bits
These bits are used to identify the part number.

bit 4-0 **REV<4:0>:** Revision ID bits
These bits are used to identify the revision.

Note 1: This location cannot be written.

REGISTER 3-2: CONFIGURATION WORD 1

R/P-1	R/P-1	R/P-1	R/P-1	R/P-1	U-1
FCMEN	IESO	$\overline{\text{CLKOUTEN}}$	BOREN<1:0>		—
bit 13					bit 8

R/P-1	R/P-1	R/P-1	R/P-1	R/P-1	R/P-1	R/P-1	R/P-1
$\overline{\text{CP}}$	MCLRE	$\overline{\text{PWRTE}}$	WDTE<1:0>		FOSC<2:0>		
bit 7							bit 0

Legend:		
R = Readable bit	P = Programmable bit	U = Unimplemented bit, read as '1'
'0' = Bit is cleared	'1' = Bit is set	-n = Value when blank or after Bulk Erase

bit 13 **FCMEN:** Fail-Safe Clock Monitor Enable bit
1 = Fail-Safe Clock Monitor is enabled
0 = Fail-Safe Clock Monitor is disabled

bit 12 **IESO:** Internal External Switchover bit
1 = Internal/External Switchover mode is enabled
0 = Internal/External Switchover mode is disabled

bit 11 **$\overline{\text{CLKOUTEN}}$:** Clock Out Enable bit
1 = CLKOUT function is disabled. I/O or oscillator function on CLKOUT pin.
0 = CLKOUT function is enabled on CLKOUT pin

bit 10-9 **BOREN<1:0>:** Brown-out Reset Enable bits(1)
11 = BOR enabled
10 = BOR enabled during operation and disabled in Sleep
01 = BOR controlled by SBOREN bit of the PCON register
00 = BOR disabled

bit 8 **Unimplemented:** Read as '1'

bit 7 **$\overline{\text{CP}}$:** Code Protection bit(2)
1 = Program memory code protection is disabled
0 = Program memory code protection is enabled

bit 6 **MCLRE:** $\overline{\text{MCLR}}$/VPP Pin Function Select bit
If LVP bit = 1:
This bit is ignored.
If LVP bit = 0:
1 = $\overline{\text{MCLR}}$/VPP pin function is $\overline{\text{MCLR}}$; Weak pull-up enabled.
0 = $\overline{\text{MCLR}}$/VPP pin function is digital input; $\overline{\text{MCLR}}$ internally disabled; Weak pull-up under control of WPUA register.

bit 5 **$\overline{\text{PWRTE}}$:** Power-up Timer Enable bit(1)
1 = PWRT disabled
0 = PWRT enabled

bit 4-3 **WDTE<1:0>:** Watchdog Timer Enable bit
11 = WDT enabled
10 = WDT enabled while running and disabled in Sleep
01 = WDT controlled by the SWDTEN bit in the WDTCON register
00 = WDT disabled

bit 2-0 **FOSC<2:0>:** Oscillator Selection bits
111 = ECH: External Clock, High-Power mode: on CLKIN pin
110 = ECM: External Clock, Medium-Power mode: on CLKIN pin
101 = ECL: External Clock, Low-Power mode: on CLKIN pin
100 = INTOSC oscillator: I/O function on OSC1 pin
011 = EXTRC oscillator: RC function on OSC1 pin
010 = HS oscillator: High-speed crystal/resonator on OSC2 pin and OSC1 pin
001 = XT oscillator: Crystal/resonator on OSC2 pin and OSC1 pin
000 = LP oscillator: Low-power crystal on OSC2 pin and OSC1 pin

Note 1: Enabling Brown-out Reset does not automatically enable Power-up Timer.
2: The entire program memory will be erased when the code protection is turned off.

REGISTER 3-3: CONFIGURATION WORD 2

R/P-1	R/P-1	R/P-1	R/P-1	R/P-1	U-1
LVP	$\overline{\text{DEBUG}}$	$\overline{\text{LPBOR}}$	BORV	STVREN	—
bit 13					bit 8

U-1	U-1	U-1	R/P-1	U-1	U-1	R/P-1	R/P-1
—	—	—	$\overline{\text{VCAPEN}}$(2)	—	—	WRT<1:0>	
bit 7							bit 0

Legend:		
R = Readable bit	P = Programmable bit	U = Unimplemented bit, read as '1'
'0' = Bit is cleared	'1' = Bit is set	-n = Value when blank or after Bulk Erase

bit 13 **LVP:** Low-Voltage Programming Enable bit(1)
1 = Low-voltage programming enabled
0 = HV on $\overline{\text{MCLR}}$/VPP must be used for programming

bit 12 **$\overline{\text{DEBUG}}$:** In-Circuit Debugger Mode bit
1 = In-Circuit Debugger disabled, ICSPCLK and ICSPDAT are general purpose I/O pins
0 = In-Circuit Debugger enabled, ICSPCLK and ICSPDAT are dedicated to the debugger

bit 11 **$\overline{\text{LPBOR}}$:** Low-Power BOR
1 = Low-Power BOR is disabled
0 = Low-Power BOR is enabled

bit 10 **BORV:** Brown-out Reset Voltage Selection bit
1 = Brown-out Reset voltage (VBOR), low trip point selected
0 = Brown-out Reset voltage (VBOR), high trip point selected

bit 9 **STVREN:** Stack Overflow/Underflow Reset Enable bit
1 = Stack Overflow or Underflow will cause a Reset
0 = Stack Overflow or Underflow will not cause a Reset

bit 8-5 **Unimplemented:** Read as '1'

bit 4 **$\overline{\text{VCAPEN}}$:** Voltage Regulator Capacitor Enable bits(1)
0 = VCAP functionality is enabled on VCAP pin
1 = All VCAP pin functions are disabled

bit 3-2 **Unimplemented:** Read as '1'

bit 1-0 **WRT<1:0>:** Flash Memory Self-Write Protection bits
2 kW Flash memory (PIC16(L)F1512):
11 = Write protection off
10 = 000h to 1FFh write-protected, 200h to 7FFh may be modified by PMCON control
01 = 000h to FFFh write-protected, 400h to 7FFh may be modified by PMCON control
00 = 000h to 7FFh write-protected, no addresses may be modified by PMCON control
4 kW Flash memory (PIC16(L)F1513):
11 = Write protection off
10 = 000h to 1FFh write-protected, 200h to FFFh may be modified by PMCON control
01 = 000h to 7FFh write-protected, 800h to FFFh may be modified by PMCON control
00 = 000h to FFFh write-protected, no addresses may be modified by PMCON control
8 kW Flash memory (PIC16F/LF1516/1517/1526):
11 = Write protection off
10 = 000h to 1FFh write-protected, 200h to 1FFFh may be modified by PMCON control
01 = 000h to FFFh write-protected, 1000h to 1FFFh may be modified by PMCON control
00 = 000h to 1FFFh write-protected, no addresses may be modified by PMCON control
16 kW Flash memory (PIC16F/LF1518/1519/1527):
11 = Write protection off
10 = 000h to 1FFh write-protected, 200h to 3FFFh may be modified by PMCON control
01 = 000h to 1FFFh write-protected, 2000h to 3FFFh may be modified by PMCON control
00 = 000h to 3FFFh write-protected, no addresses may be modified by PMCON control

Note 1: The LVP bit cannot be programmed to '0' when Programming mode is entered via LVP.
2: Applies to PIC16F151X/152X devices only. On PIC16LF151X/152X, the $\overline{\text{VCAPEN}}$ bit is unimplemented.

4.3 Program/Verify Commands

The PIC16(L)F151X/152X implements 10 programming commands; each six bits in length. The commands are summarized in Table 4-1.

Commands that have data associated with them are specified to have a minimum delay of TDLY between the command and the data. After this delay 16 clocks are required to either clock in or clock out the 14-bit data word. The first clock is for the Start bit and the last clock is for the Stop bit.

TABLE 4-1: COMMAND MAPPING

Command	Mapping							Data/Note
	Binary (MSb … LSb)						Hex	
Load Configuration	x	0	0	0	0	0	00h	0, data (14), 0
Load Data For Program Memory	x	0	0	0	1	0	02h	0, data (14), 0
Read Data From Program Memory	x	0	0	1	0	0	04h	0, data (14), 0
Increment Address	x	0	0	1	1	0	06h	—
Reset Address	x	1	0	1	1	0	16h	—
Begin Internally Timed Programming	x	0	1	0	0	0	08h	—
Begin Externally Timed Programming	x	1	1	0	0	0	18h	—
End Externally Timed Programming	x	0	1	0	1	0	0Ah	—
Bulk Erase Program Memory	x	0	1	0	0	1	09h	Internally Timed
Row Erase Program Memory	x	1	0	0	0	1	11h	Internally Timed

4.3.1 LOAD CONFIGURATION

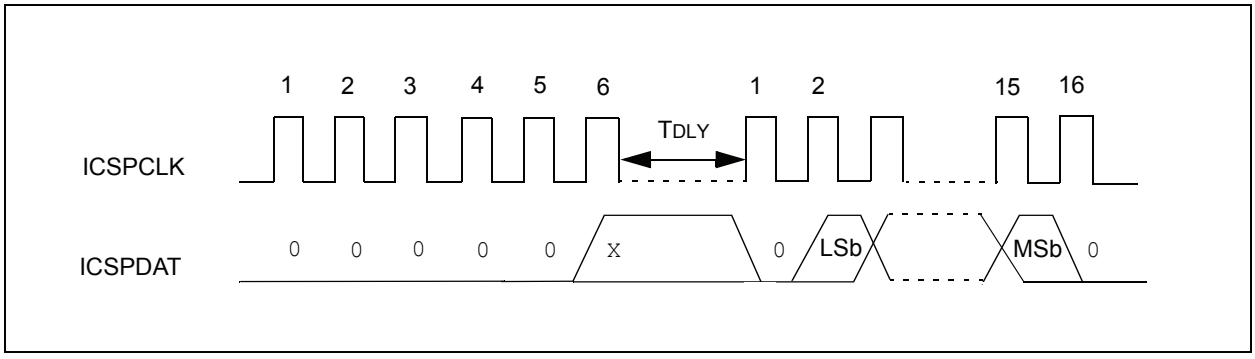
The Load Configuration command is used to access the configuration memory (User ID Locations, Configuration Words, Calibration Words). The Load Configuration command sets the address to 8000h and loads the data latches with one word of data (see Figure 4-1).

After issuing the Load Configuration command, use the Increment Address command until the proper address to be programmed is reached. The address is then programmed by issuing either the Begin Internally Timed Programming or Begin Externally Timed Programming command.

Note: Externally timed writes are not supported for Configuration and Calibration bits. Any externally timed write to the Configuration or Calibration Word will have no effect on the targeted word.

The only way to get back to the program memory (address 0) is to exit Program/Verify mode or issue the Reset Address command after the configuration memory has been accessed by the Load Configuration command.

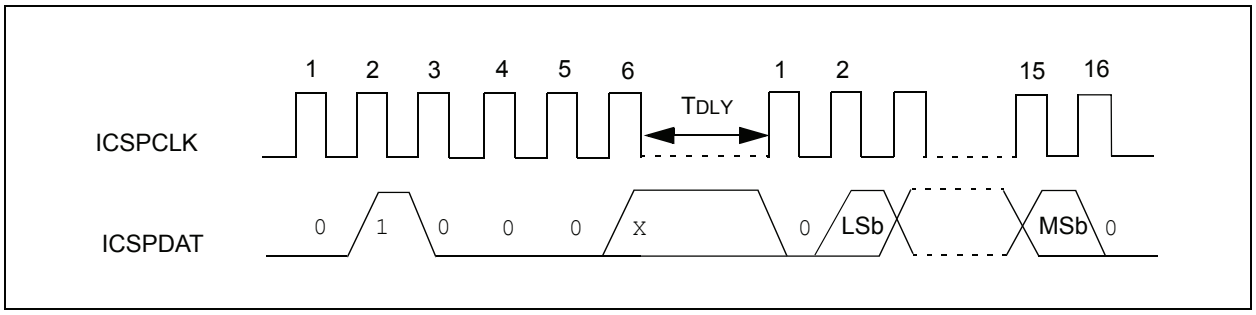
FIGURE 4-1: LOAD CONFIGURATION



4.3.2 LOAD DATA FOR PROGRAM MEMORY

The Load Data for Program Memory command is used to load one 14-bit word into the data latches. The word programs into program memory after the Begin Internally Timed Programming or Begin Externally Timed Programming command is issued (see Figure 4-2).

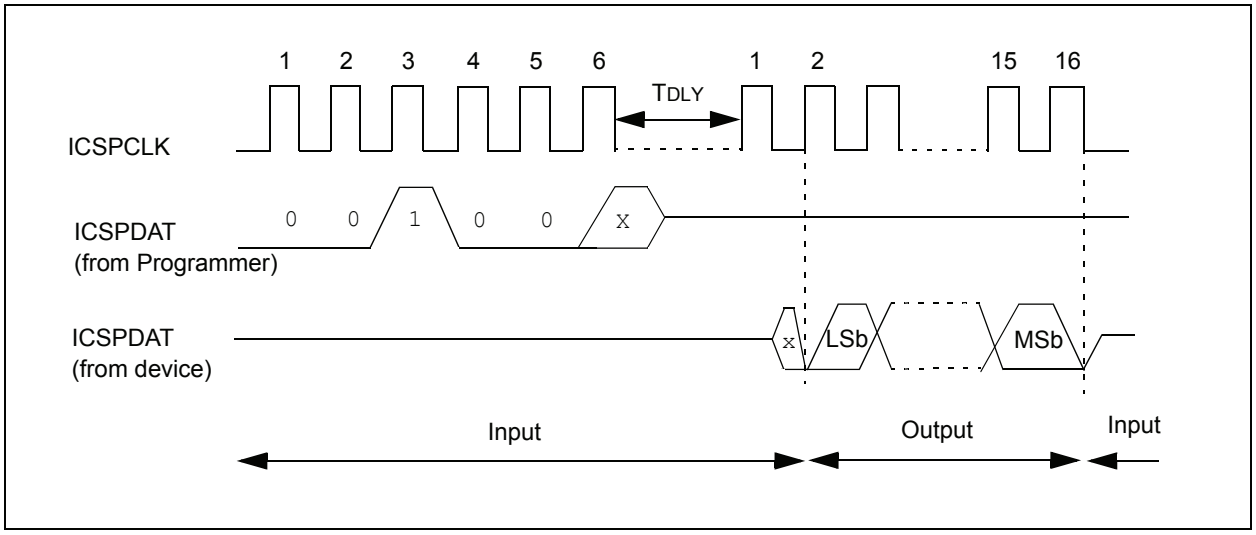
FIGURE 4-2: LOAD DATA FOR PROGRAM MEMORY



4.3.3 READ DATA FROM PROGRAM MEMORY

The Read Data from Program Memory command will transmit data bits out of the program memory map currently accessed, starting with the second rising edge of the clock input. The ICSPDAT pin will go into Output mode on the first falling clock edge, and it will revert to Input mode (high-impedance) after the 16th falling edge of the clock. If the program memory is code-protected ($\overline{CP}$), the data will be read as zeros (see Figure 4-3).

FIGURE 4-3: READ DATA FROM PROGRAM MEMORY



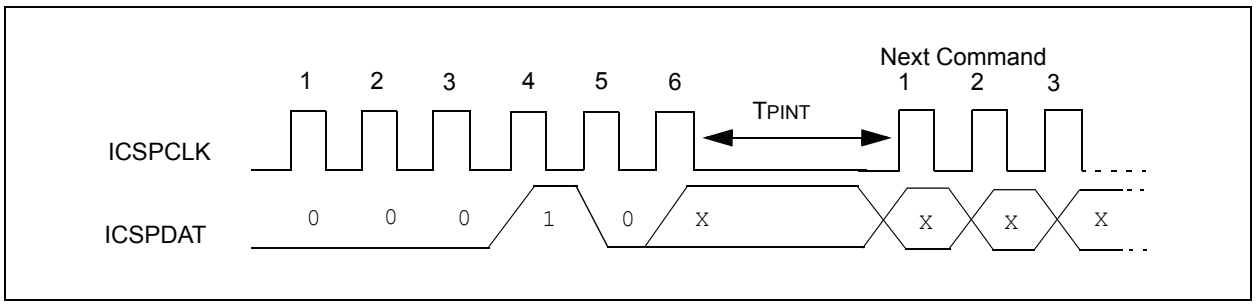
4.3.6 BEGIN INTERNALLY TIMED PROGRAMMING

A Load Configuration or Load Data for Program Memory command must be given before every Begin Programming command. Programming of the addressed memory will begin after this command is received. An internal timing mechanism executes the write. The user must allow for the program cycle time, TPINT, for the programming to complete.

The End Externally Timed Programming command is not needed when the Begin Internally Timed Programming is used to start the programming.

The program memory address that is being programmed is not erased prior to being programmed.

FIGURE 4-6: BEGIN INTERNALLY TIMED PROGRAMMING

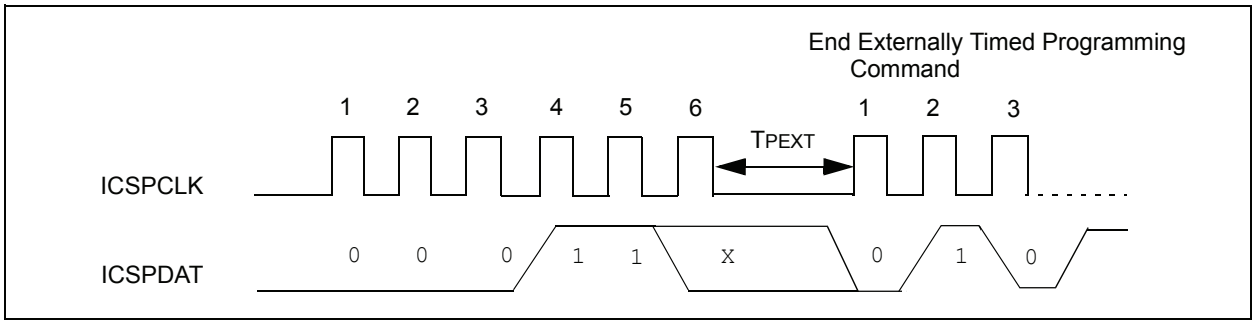


4.3.7 BEGIN EXTERNALLY TIMED PROGRAMMING

A Load Configuration or Load Data for Program Memory command must be given before every Begin Programming command. Programming of the addressed memory will begin after this command is received. To complete the programming the End Externally Timed Programming command must be sent in the specified time window defined by TPEXT (see Figure 4-7).

Externally timed writes are not supported for Configuration and Calibration bits. Any externally timed write to the Configuration or Calibration Word will have no effect on the targeted word.

FIGURE 4-7: BEGIN EXTERNALLY TIMED PROGRAMMING



4.3.10 ROW ERASE PROGRAM MEMORY

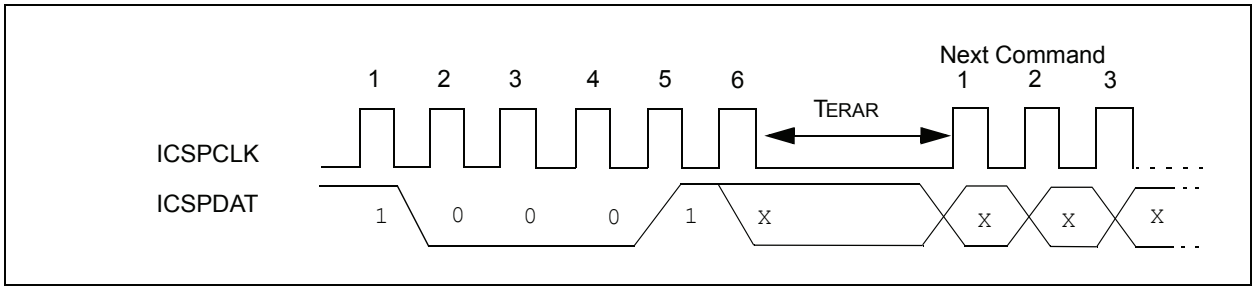
The Row Erase Program Memory command will erase an individual row. Refer to Table 4-2 for row sizes of specific devices and the PC bits used to address them. If the program memory is code-protected the Row Erase Program Memory command will be ignored. When the address is 8000h-8008h the Row Erase Program Memory command will only erase the user ID locations regardless of the setting of the $\overline{CP}$ Configuration bit.

After receiving the Row Erase Program Memory command the erase will not complete until the time interval, TERAR, has expired.

TABLE 4-2: PROGRAMMING ROW SIZE AND LATCHES

Devices	PC	Row Size	Number of Latches
PIC16(L)F151X/152X	<15:5>	32	32

FIGURE 4-10: ROW ERASE PROGRAM MEMORY



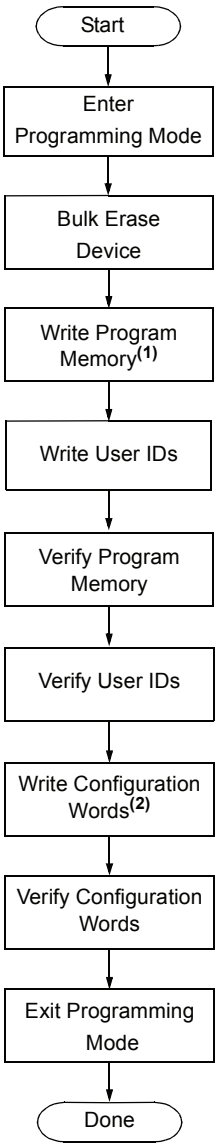
5.0 PROGRAMMING ALGORITHMS

The devices use internal latches to temporarily store the 14-bit words used for programming. Refer to Table 4-2 for specific latch information. The data latches allow the user to write the program words with a single Begin Externally Timed Programming or Begin Internally Timed Programming command. The Load Program Data or the Load Configuration command is used to load a single data latch. The data latch will hold the data until the Begin Externally Timed Programming or Begin Internally Timed Programming command is given.

The data latches are aligned with the LSbs of the address. The PC's address at the time the Begin Externally Timed Programming or Begin Internally Timed Programming command is given will determine which location(s) in memory are written. Writes cannot cross the physical boundary. For example, with the PIC16F1527, attempting to write from address 0002h-0009h will result in data being written to 0008h-000Fh.

If more than the maximum number of data latches are written without a Begin Externally Timed Programming or Begin Internally Timed Programming command, the data in the data latches will be overwritten. The following figures show the recommended flowcharts for programming.

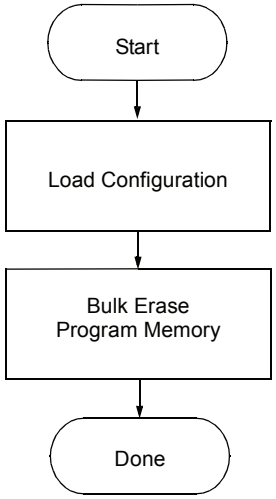
FIGURE 5-1: DEVICE PROGRAM/VERIFY FLOWCHART



Note 1: See Figure 5-2.

2: See Figure 5-5.

FIGURE 5-6: ERASE FLOWCHART



Note: This sequence does not erase the Calibration Words.

8.0 ELECTRICAL SPECIFICATIONS

Refer to device specific data sheet for absolute maximum ratings.

TABLE 8-1: AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/VERIFY MODE

AC/DC CHARACTERISTICS			Standard Operating Conditions Production tested at 25°C				
Sym.	**Characteristics**		**Min.**	**Typ.**	**Max.**	**Units**	**Conditions/Comments**
Supply Voltages and Currents							
V_{DD}	Supply Voltage (V_{DDMIN}, V_{DDMAX})	PIC16F151X PIC16F152X	2.3	—	5.5	V	
		PIC16LF151X PIC16LF152X	1.8	—	3.6	V	
V_{PEW}	Read/Write and Row Erase operations		V_{DDMIN}	—	V_{DDMAX}	V	
V_{PBE}	Bulk Erase operations		2.7	—	V_{DDMAX}	V	
I_{DDI}	Current on V_{DD}, Idle		—	—	1.0	mA	
I_{DDP}	Current on V_{DD}, Programming		—	—	3.0	mA	
	V_{PP}						
I_{PP}	Current on $\overline{MCLR}/V_{PP}$		—	—	600	μA	
V_{IHH}	High voltage on $\overline{MCLR}/V_{PP}$ for Program/Verify mode entry		8.0	—	9.0	V	
T_{VHHR}	$\overline{MCLR}$ rise time (V_{IL} to V_{IHH}) for Program/Verify mode entry		—	—	1.0	μs	
	I/O pins						
V_{IH}	(ICSPCLK, ICSPDAT, $\overline{MCLR}/V_{PP}$) input high level		0.8 V_{DD}	—	—	V	
V_{IL}	(ICSPCLK, ICSPDAT, $\overline{MCLR}/V_{PP}$) input low level		—	—	0.2 V_{DD}	V	
V_{OH}	ICSPDAT output high level		V_{DD}-0.7 V_{DD}-0.7 V_{DD}-0.7	—	—	V	I_{OH} = 3.5 mA, V_{DD} = 5V I_{OH} = 3 mA, V_{DD} = 3.3V I_{OH} = 2 mA, V_{DD} = 1.8V
V_{OL}	ICSPDAT output low level		—	—	V_{SS}+0.6 V_{SS}+0.6 V_{SS}+0.6	V	I_{OH} = 8 mA, V_{DD} = 5V I_{OH} = 6 mA, V_{DD} = 3.3V I_{OH} = 3 mA, V_{DD} = 1.8V
Programming Mode Entry and Exit							
T_{ENTS}	Programing mode entry setup time: ICSPCLK, ICSPDAT setup time before V_{DD} or $\overline{MCLR}$↑		100	—	—	ns	
T_{ENTH}	Programing mode entry hold time: ICSPCLK, ICSPDAT hold time after V_{DD} or $\overline{MCLR}$↑		250	—	—	μs	
Serial Program/Verify							
T_{CKL}	Clock Low Pulse Width		100	—	—	ns	
T_{CKH}	Clock High Pulse Width		100	—	—	ns	
T_{DS}	Data in setup time before clock↓		100	—	—	ns	
T_{DH}	Data in hold time after clock↓		100	—	—	ns	
T_{CO}	Clock↑ to data out valid (during a Read Data command)		0	—	80	ns	
T_{LZD}	Clock↓ to data low-impedance (during a Read Data command)		0	—	80	ns	
T_{HZD}	Clock↓ to data high-impedance (during a Read Data command)		0	—	80	ns	
T_{DLY}	Data input not driven to next clock input (delay required between command/data or command/command)		1.0	—	—	μs	
T_{ERAB}	Bulk Erase cycle time		—	—	5	ms	
T_{ERAR}	Row Erase cycle time		—	—	2.5	ms	

Note 1: Externally timed writes are not supported for Configuration and Calibration bits.

TABLE 8-1: AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/VERIFY

AC/DC CHARACTERISTICS		Standard Operating Conditions Production tested at 25°C				
Sym.	**Characteristics**	**Min.**	**Typ.**	**Max.**	**Units**	**Conditions/Comments**
TPINT	Internally timed programming operation time	— —	— —	2.5 5	ms ms	Program memory Configuration Words
TPEXT	Externally timed programming pulse	1.0	—	2.1	ms	**Note 1**
TDIS	Time delay from program to compare (HV discharge time)	300	—	—	μs	
TEXIT	Time delay when exiting Program/Verify mode	1	—	—	μs	

Note 1: Externally timed writes are not supported for Configuration and Calibration bits.

8.1 AC Timing Diagrams

FIGURE 8-1: PROGRAMMING MODE ENTRY – VDD FIRST

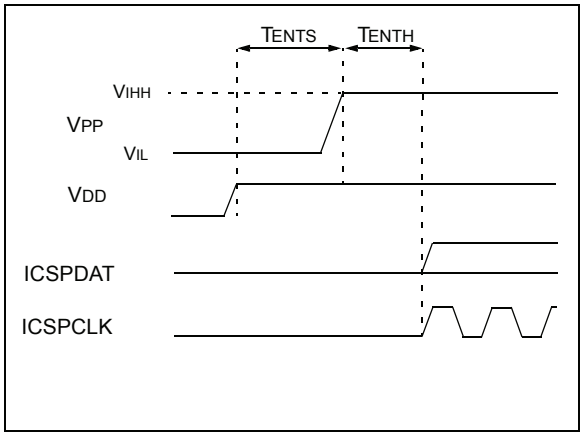


FIGURE 8-2: PROGRAMMING MODE ENTRY – VPP FIRST

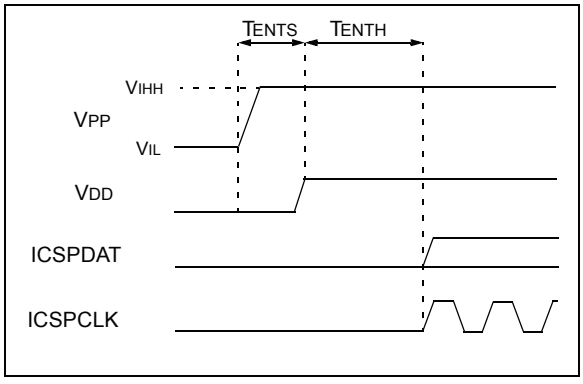


FIGURE 8-3: PROGRAMMING MODE EXIT – VPP LAST

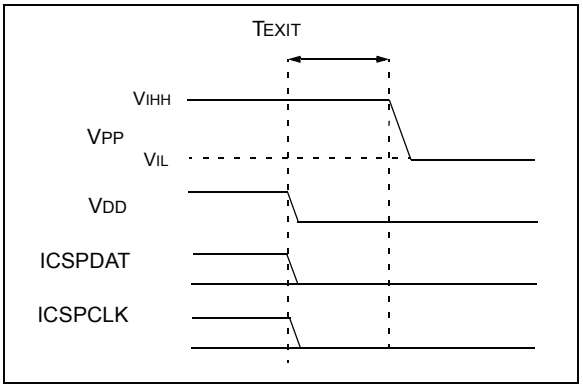
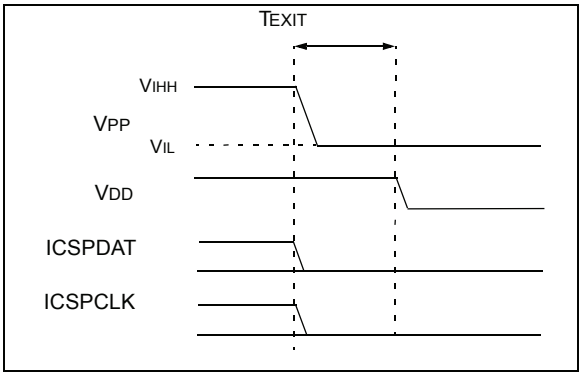


FIGURE 8-4: PROGRAMMING MODE EXIT – VDD LAST



APPENDIX A: REVISION HISTORY

Revision A (08/2010)

Original release of this document.

Revision B (09/2011)

Added PIC16(L)F1512/1513 devices; Added new Figures 3-1 and 3-2; Updated Registers 3-1, 3-2 and 3-3 to new format; Updated Register 3-3 to add 2 kW and 4 kW Flash memory; Added Notes to Examples 7-1 to 7-4; Updated Table 8-1; Other minor corrections.

NOTES:

Note the following details of the code protection feature on Microchip devices:

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